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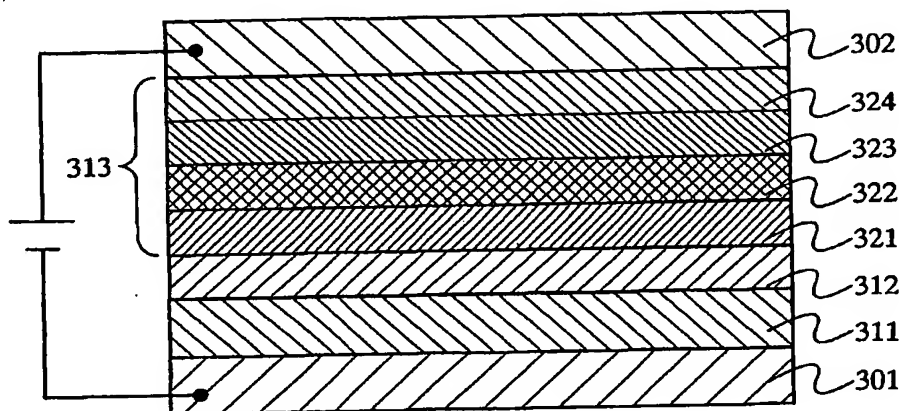
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(54) Title: LIGHT-EMITTING ELEMENT AND LIGHT EMITTING DEVICE USING THE SAME



**(57) Abstract:** The present invention provides a light-emitting element having less increase in driving voltage with the accumulation of light-emission time, and provides a light-emitting element having less increase in resistance value with the increase in film thickness. A light-emitting element includes a first layer, a second layer and a third layer between a first electrode and a second electrode. The first layer is provided to be closer to the first electrode than the second layer, and the third layer is provided to be closer to the second electrode than the second layer. The first layer is a layer including an aromatic amine compound and a substance showing an electron accepting property to the aromatic amine compound. The second layer includes a substance of which an electron transporting property is stronger than a hole transporting property, and a substance showing an electron donating property to the aforementioned substance.

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